## SILICON PNP TRIPLE DIFFUSED TYPE

# 2SA1265

#### POWER AMPLIFIER APPLICATIONS.

#### FEATURES:

- . Complementary to 2SC3182
- . Recommend for 70W High Fidelity
  Audio Frequency Amplifier Output Stage

## MAXIMUM RATINGS (Ta=25°C)

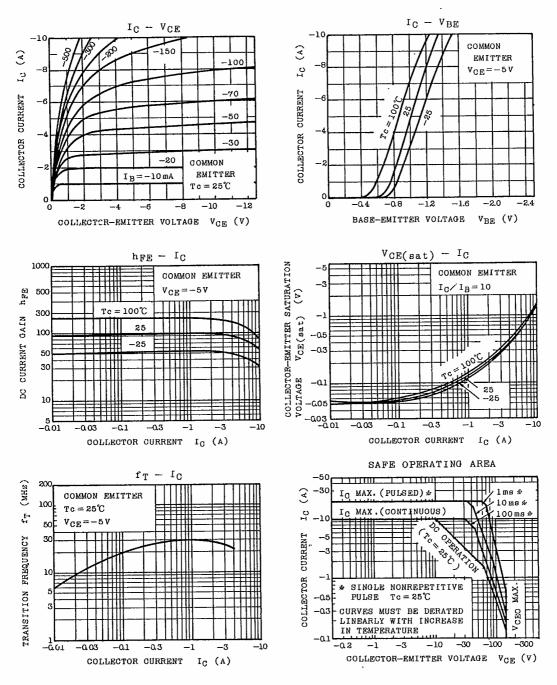
CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v <sub>CBO</sub>	-140	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-140	V
Emitter-Base Voltage	VEBO	5	V
Collector Current	IC	-10	A
Base Current	IB	-1	A
Collector Power Dissipation (Tc=25°C)	PC	100	W
Junction Temperature	Tj	150	°c
Storage Temperature Range	Tstg	-55~150	°c

Weight : 4.6g

# ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	V <sub>CB</sub> =-140V, I <sub>E</sub> =0			-5.0	μA
Emitter Cut-off Current	IEBO	VEB=-5V, IC=0			-5.0	μA
Collector-Emitter Breakdown Voltage	V(BR)CEO	I <sub>C</sub> =-50mA, I <sub>B</sub> =0	-140	-	-	V
DC Current Gain	hFE(1) (Note)	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A	55	-	160	
	hFE(2)	V <sub>CE</sub> =-5V, I <sub>C</sub> =-5A	35	83	-	
Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =-7A, I <sub>B</sub> =-0.7A	-	-0.8	-2.0	V
Base-Emitter Voltage	VBE	V <sub>CE</sub> =-5V, I <sub>C</sub> =-5A	<u> </u>	-1.0	-1.5	v
Transition Frequency	f <sub>T</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A		30		MHz
Collector Output Capacitance	Cob	$V_{CB}$ =-10V, $I_{E}$ =0, $f$ =1MHz	-	480	-	pF

Note: hFE(1) Classification R: 55~110, 0: 80~160



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